

- ☞ L11: (8456) L10 near3 L1
- ☞ L12: (742) L11 same L5
- ☞ L13: (92) L9 and L12
- ☞ L14: (92) L13 and L10
- ☞ L15: (4347864) contact electrode
- ☞ L16: (281295) L15 near9 L3
- ☞ L17: (87) L16 and L14
- ☞ L18: (13) Forward citation search 1
- ☞ L19: (13) Forward citation search 2
- ☞ L20: (4504) 1 near 10
- ☞ L21: (17040) locos
- ☞ L22: (171) 20 and 21
- ☞ L23: (184) 22 and 15
- ☞ L24: (94) 23 and 8
- ☞ L25: (2146) 2 with 21
- ☞ L26: (24) 24 and 25
- ☞ L27: (24) 28 and 10
- ☞ L28: (24) 27 and 2
- ☞ L29: (1424) 20.ab
- ☞ L30: (306) 21 with 3
- ☞ L31: (11) 29 and 30
- ☞ L32: (23) 29 and 21
- ☞ L33: (262) (257/380).CCLS.
- ☞ L34: (23) 33 and 21

Doc: XEROX, L1, L10, L11, L12, L13, L14, L15, L16, L17, L18, L19, L20, L21, L22, L23, L24, L25, L26, L27, L28, L29, L30, L31, L32, L33, L34

Search: [XEROX]

L16 and L14

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	U	Inventor	Document ID	Issue P	Title	Current	Current X	Retrieval	S	C	P	Image	Doc
1	<input checked="" type="checkbox"/>	Lasky, Jero	US 5888875 A	1999	8	Diffusion resistor structure with silicide	438/38	257/E21.3	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 5888875
2	<input checked="" type="checkbox"/>	Usuki, Hide	US 5377140 A	1994	1	Cell for random access memory	385/15	257/538	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 5377140
3	<input checked="" type="checkbox"/>	Takeda, Ka	US 4898837 A	1990	1	Method of fabricating a semiconductor	438/33	257/539	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 4898837
4	<input checked="" type="checkbox"/>	Langdon, J	US 3729662 A	1973	5	SEMICONDUCTOR RESISTOR	257/53	148/DIG.3	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 3729662
5	<input checked="" type="checkbox"/>	Liou, Jhyy	US 20040217379 A	2004	1	Compact mask programmable rom	257/20		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040217379
6	<input checked="" type="checkbox"/>	Voldman, S	US 6465870 B2	2002	1	ESD robust silicon germanium transist	257/56	257/197	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6465870
7	<input checked="" type="checkbox"/>	Yu, Allen S	US 6287922 B1	2001	4	Method for fabricating graded LDD tra	438/29	257/E21.2	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6287922
8	<input checked="" type="checkbox"/>	Sato, Tetsu	US 20040232453 A	2004	3	Method for manufacturing a semicond	257/22		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040232453
9	<input checked="" type="checkbox"/>	Hall, Jeffer	US 6362067 B1	2002	6	Accurate self-aligned resistor structur	438/38	257/E27.0	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6362067
10	<input checked="" type="checkbox"/>	Komori, Shi	US 20040248358 A	2004	2	MANUFACTURING METHOD OF A SE	438/23		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20040248358